

**Amendments to the Specification:**

Please replace the title as follows:

~~SILICON SINGLE CRYSTAL, SILICON WAFER, PRODUCTION APPARATUS  
THEREFOR AND PROCESS FOR PRODUCING THE SAME~~

A SILICON SINGLE CRYSTAL, A SILICON WAFER, AN APPARATUS FOR  
PRODUCING THE SAME, AND A METHOD FOR PRODUCING THE SAME

Please replace the paragraph beginning on page 23, line 10, with the following rewritten paragraph:

Moreover, the present invention provides a method for producing a silicon single crystal by using a combined apparatus of at least two or more of the producing apparatus in which Cu concentration in a component made of quartz is determined, the producing apparatus in which Cu in devices and the like to be exposed in the furnace is determined, and the producing ~~method~~-apparatus in which Cu concentration of an observation window made of quartz is determined. Furthermore, the present invention provides a method for producing a silicon single crystal, wherein a silicon single crystal is grown by a combined method of the method for performing heating with a heating heater after melting of raw material and the method for cleaning HZ components in a clean environment.